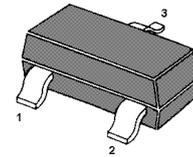


PNP Silicon Epitaxial Planar Transistor

for high voltage .



1.Base 2.Emitter 3.Collector
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

| Parameter | Symbol | Value | Unit |
|------------------------------|------------|-------------|------------------|
| Collector Base Voltage | $-V_{CBO}$ | 130 | V |
| Collector Emitter Voltage | $-V_{CEO}$ | 120 | V |
| Emitter Base Voltage | $-V_{EBO}$ | 5 | V |
| Collector Current Continuous | $-I_C$ | 600 | mA |
| Power Dissipation | P_{tot} | 200 | mW |
| Junction Temperature | T_J | 150 | $^\circ\text{C}$ |
| Storage Temperature Range | T_S | -55 to +150 | $^\circ\text{C}$ |

Characteristics at $T_{amb}=25^{\circ}\text{C}$

| Parameter | Symbol | Min. | Max. | Unit |
|---|----------------|------|------|---------------|
| DC Current Gain at $-V_{CE}=5\text{V}$, $-I_C=10\text{mA}$ | h_{FE} | 40 | 180 | - |
| Collector Base Breakdown Voltage at $-I_C=0.1\text{mA}$ | $-V_{(BR)CBO}$ | 130 | - | V |
| Collector Emitter Breakdown Voltage at $-I_C=1\text{mA}$ | $-V_{(BR)CEO}$ | 120 | - | V |
| Emitter Base Breakdown Voltage at $-I_E=0.1\text{mA}$ | $-V_{(BR)EBO}$ | 5 | - | V |
| Collector Cutoff Current at $-V_{CB}=100\text{V}$ | $-I_{CBO}$ | - | 0.05 | μA |
| Emitter Cutoff Current at $-V_{EB}=3\text{V}$ | $-I_{EBO}$ | - | 0.05 | μA |
| Collector Emitter Saturation Voltage at $-I_C=50\text{mA}$, $-I_B=5\text{mA}$ | $-V_{CE(sat)}$ | - | 0.5 | V |
| Base Emitter Saturation Voltage at $-I_C=50\text{mA}$, $-I_B=5\text{mA}$ | $-V_{BE(sat)}$ | - | 1 | V |
| Current Gain Bandwidth Product at $-V_{CE}=10\text{V}$, $-I_C=10\text{mA}$ | f_T | 100 | - | MHz |
| Output Capacitance at $-V_{CB}=10\text{V}$, $f=1\text{MHz}$ | C_{ob} | - | 6 | pF |
| Noise Figure at $-I_C=0.2\text{mA}$, $-V_{CE}=5\text{V}$, $f=15.7\text{KHz}$ | NF | - | 8 | dB |